8/10/24 Diode: -> small electronic component that allows electricity to flow thorugh it in only one direction ( wie a one-way Street for electric current) >Two terminals: ) Anode (tre) 2) cathodo (-ve) 101 - W > current flow. When the anode is more positive than and cathode the dode allows current to pass (forward bias When anode is less than cathode, it blocks werent Perus (en) Plumbing the water flows only in one direction, other way it stops ( Diode stops electricity when it is in wrong direction symbol. > | Arrow pointing towards diode arrow indicates the direction of flow of current ( Anode to cathode practical use: 1) Rectification (Ac to Dc conversion) -> This is commonly found in adapters and power supplies to convert the Ac vollage from wall socket into Dc vollage suitable for electronic devices. 2) LED - Indicator lights, displays and lighting 3) voltage Regulation (zenerdiode) -> Jener diode are used in voltage regulation xir cuits to maintain a constant voltage across a load, even when the input voltage fluctuates. They operate in Reverse bies mode 1) signal Demodulation: (Diode Detector) - It is used in Radio receiver to entract the audio signal from the modulated carrier wave this process demodulation. Dide coystal radio set detects called the audio signil from radio waves enabling you to lister to vadio stations 5) Revere vollage protection: -> Diodes are placed in series with the power supply to prevent damage when a battery or power source connected backward. The diode blocks if the polarity is reverse based

	Later limiting
	1) Clamping circuity -> Diodes are used for voltage limiting  T) suitching Applications ( Digital logic clocuits)
-J 91.	1) suitching Applications ( Digital logue clouds)
\$ 1 th	1) Clamping circuity -> Diocles Are  1) Switching Applications ( Digital logic crowds)  8) voltage multiplication ( high voltage circuits)  (to generate high Dic voltage from Low Miney)
( MATCH	(to generate high October)
<u> </u>	PN Junction: Diode  Ot is created when p-type semiconductor devices i,  ot is created when p-type semiconductor.
	It is created when P-type see
\$1/34/37	joined with an notype semiconductor.
	joined with an n-type semiconateur.  n-diffuse into p-side and comb iro with the holes.  n-diffuse into p-side and comb iro with the holes.
	creating a depletion region.
	V A
	potential barner (Ve) 0.3v for germanium
	i) operation of PN Junction
	i) operation of pN Junion
a) No bias condition (with out an enternal voltage)	
	Minority corners on eitherside are attracted
	to the junction, balancing drift and diffusion
1	to the function, but sty
14-	current 1000 and 1400
F 32	b) forward bias condition  P side is connected to a tre terminal and the
	n-side to a negative term inal -> potential barries
All Tardus	deeneares
	Shock (ou diada T = To ( nvT - 1)
	shock by diode I = Is (envT -1)
	I = Diode current
1111 4	Is -> reverse saturation current
B 42-41.	V- Applied rolling
	n- Ideality fisher (
	n- Odeality factor (typically, for silicondiades)  Vt - Thermal voltage
and the second	Vt - Thermal voltage.
	-> D'odes shows low zeristance in the
10111	forward bias
E DAR	forward bias
120	white was the many of the state



() Roverse bias:	
p is connected to a negative term n-side to a tre terminal, the potentia	rinal and the
n-side to a tre terminal, the potentia	I barries increases
The diode shows high presistant	e and blocks
the current flow -	
Diode current Equation I=Is (e /nv1-	r) -> 0
pepletion width(w)	
$W: \sqrt{\frac{2}{2}(V_0+V)} \left(\frac{1}{V_A} + \frac{1}{V_A}\right)$	$(L) \rightarrow \emptyset$
4 ( 1971 - N	
E-Pernitivity of semiconductor	
9- electronic charge	
Vo-built in potential	
NA, ND - doping concentrations of pa	and n regions
	J
small signal resistance rd: nVT	
I D	
ID -> DC bias current	



